Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	2	("6476988").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/28 14:24
S95	53	(hydrophob\$3) with bank and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 16:19
S94	269	(hydrophob\$3) and tft and bank	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 16:18
S91	405	(hydrophob\$3 hydrophil\$3) and tft and bank	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 16:15
S93	88	S91 and (Uv and (oxygen "O.sub. 2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:22
S92	71	S91 and (Uv and (oxygen near3 plasma "O.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:22
S83	24	(Uv near3 radiation and (oxygen near3 plasma "O.sub.2")) with (substrate wafer) and (ink near3 jet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:22
S84	15879	((Uv near3 radiation and (oxygen near3 plasma "O.sub.2")) with (substrate wafer)) or (hydrophob\$3 hydrophil\$3) and (ink near3 jet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:21

S90	11	freeze near3 drying with emitt\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:17
S89	0	freeze near3 drying with tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:17
S88	0	freeze near3 drying with (cathode electrode annonde) and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:16
S87	54	freeze near3 drying with (cathode electrode annonde)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:16
S86	3029	(((Uv near3 radiation and (oxygen near3 plasma "O.sub.2")) with (substrate wafer)) or (hydrophob\$3 hydrophil\$3)) and (ink near3 jet) and (glass or acry\$3) near3 (substrate wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:12
S85	15688	(((Uv near3 radiation and (oxygen near3 plasma "O.sub.2")) with (substrate wafer)) or (hydrophob\$3 hydrophil\$3)) and (ink near3 jet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 14:11
S80	215	(Uv near3 radiation and (oxygen near3 plasma "O.sub.2")) with (substrate wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 13:55
S82	5	(Uv near3 radiation and (oxygen near3 plasma "O.sub.2")) with affinity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 10:49

		77				
S81	2	("20040245903").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/27 10:03
S79	409	S78 and ((@ad<"20040325") or (@rlad<"20040325"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/27 09:55
S78	467	S77 and (annode cathode electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:58
S74	4538	S73 and ((@ad<"20040325") or (@rlad<"20040325"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:58
S77	824	(UV and (Oxygen near3 plasma "O. sub.2")) same glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:57
S76	2	("20040245903").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/26 10:56
S75	8	(lyophiliz\$3 and lyophob\$3) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:45
S73	4980	(lyophiliz\$3 lyophob\$3) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:33

S72	13	S71 and ((@ad<"20040325") or (@rlad<"20040325"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:33
S71	50	(lyophiliz\$3 lyophob\$3) and electrode and electro\$3 near3 emitter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:32
S70	4980	(lyophiliz\$3 lyophob\$3) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:12
S69	72256	lyophiliz\$3 lyophob\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 10:11
S1	109361	tft or thin adj film adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/12/26 09:46